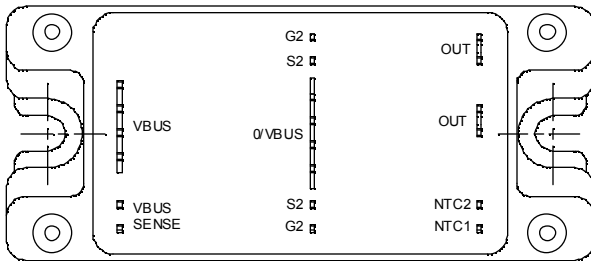
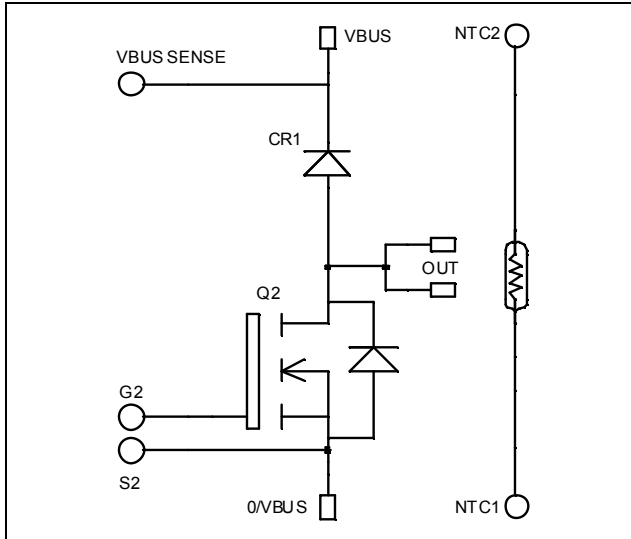


Boost chopper MOSFET Power Module

$V_{DSS} = 200V$

$R_{DSon} = 8m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 208A$ @ $T_c = 25^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	832	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	10	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ $T_j = 25^\circ\text{C}$			150	μA
		$V_{GS} = 0V, V_{DS} = 160V$ $T_j = 125^\circ\text{C}$			750	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 104A$		8	10	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{MHz}$		14.4		nF
C_{oss}	Output Capacitance			4.66		
C_{rss}	Reverse Transfer Capacitance			0.29		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 100V$ $I_D = 208A$		280		nC
Q_{gs}	Gate – Source Charge			106		
Q_{gd}	Gate – Drain Charge			134		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 208A$ $R_G = 2.5\Omega$		32		ns
T_r	Rise Time			64		
$T_{d(off)}$	Turn-off Delay Time			88		
T_f	Fall Time			116		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 208A, R_G = 2.5\Omega$		1698		μJ
E_{off}	Turn-off Switching Energy			1858		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 208A, R_G = 2.5\Omega$		1872		μJ
E_{off}	Turn-off Switching Energy			1972		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =200V	T _j = 25°C			500	μA
			T _j = 125°C			750	
I _F	DC Forward Current		T _c = 80°C		180		A
V _F	Diode Forward Voltage	I _F = 180A			1.1	1.15	V
		I _F = 360A			1.4		
		I _F = 180A	T _j = 125°C		0.9		
t _{rr}	Reverse Recovery Time	I _F = 180A V _R = 133V di/dt = 600A/μs	T _j = 25°C		31		ns
			T _j = 125°C		60		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		180		nC
			T _j = 125°C		750		

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	Transistor			0.16	°C/W
		Diode			0.32	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

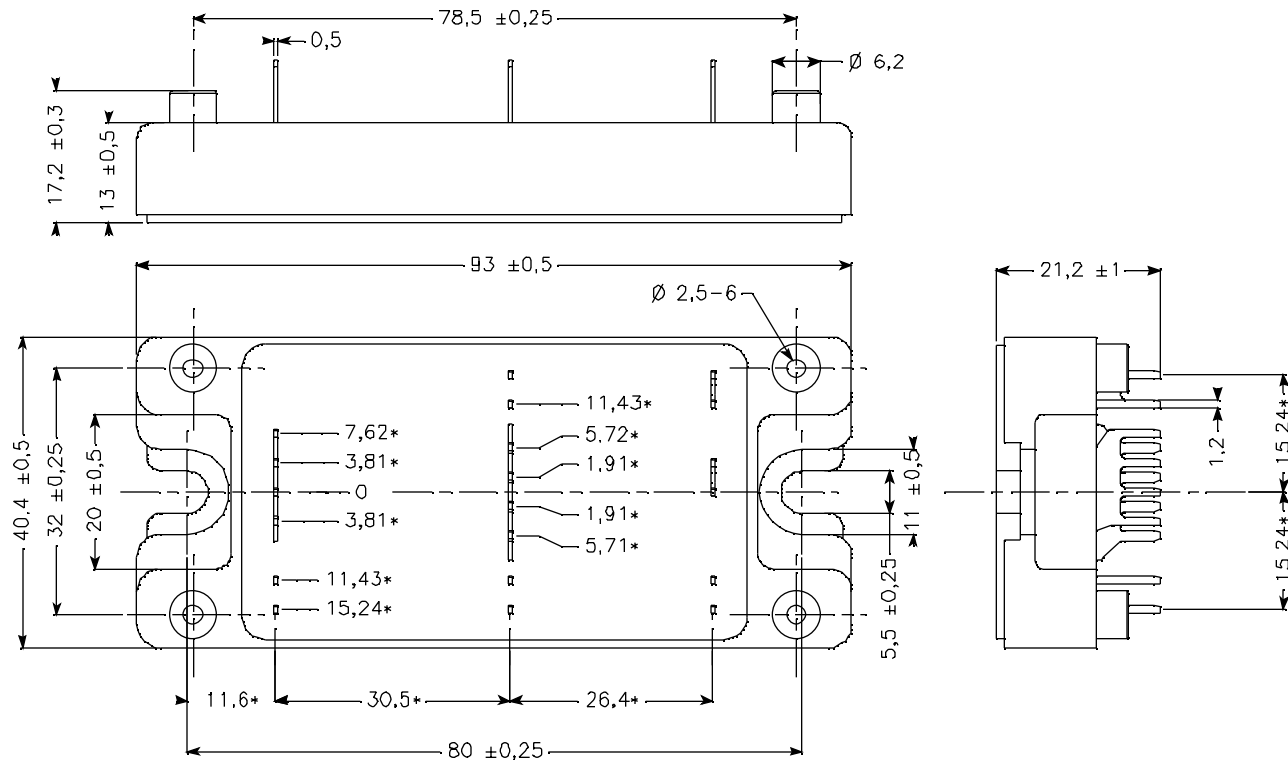
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

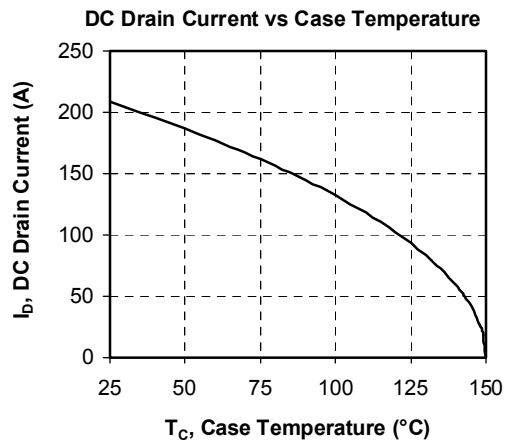
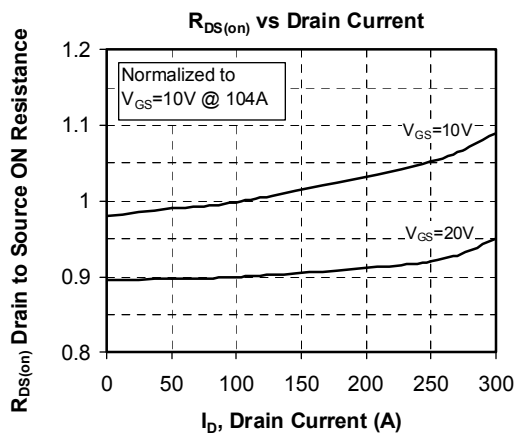
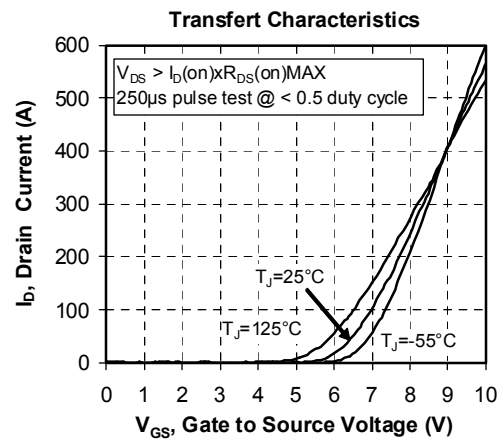
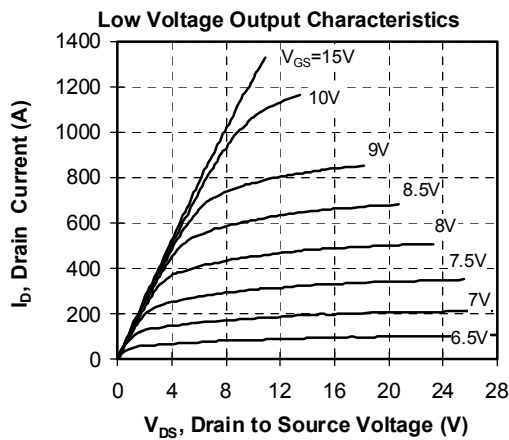
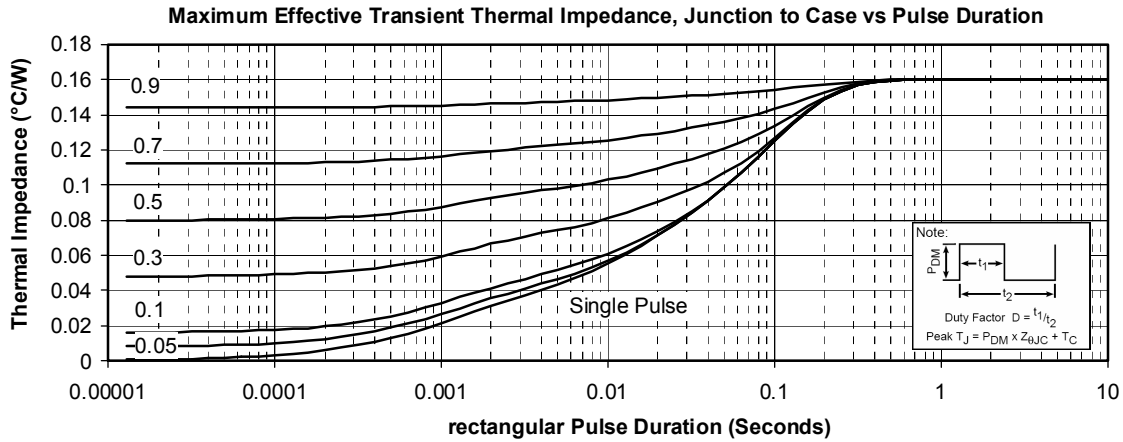
SP4 Package outline (dimensions in mm)

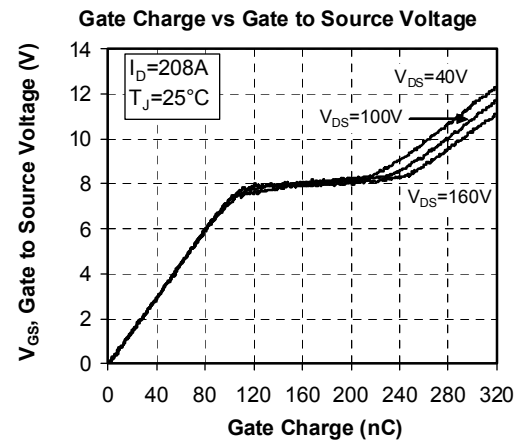
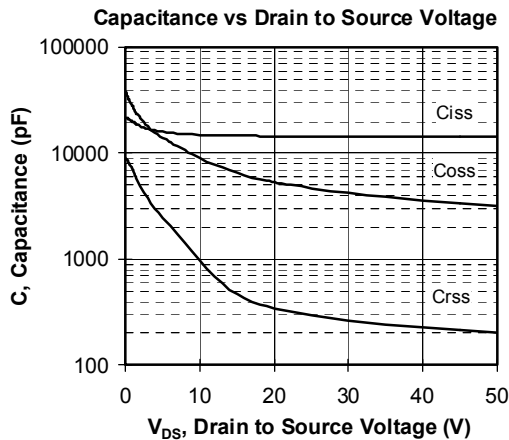
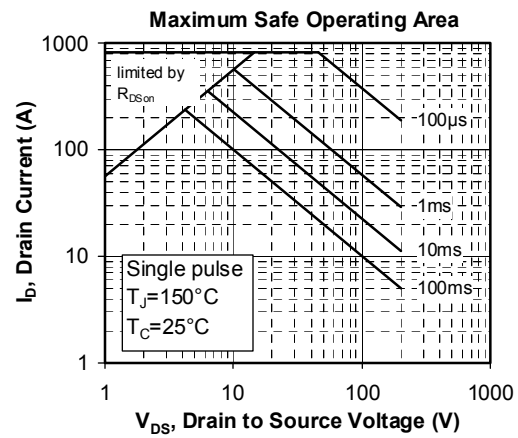
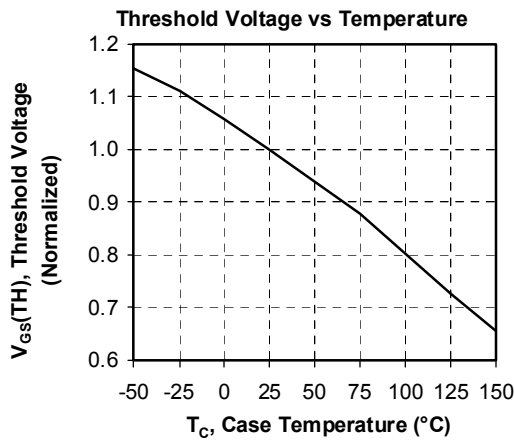
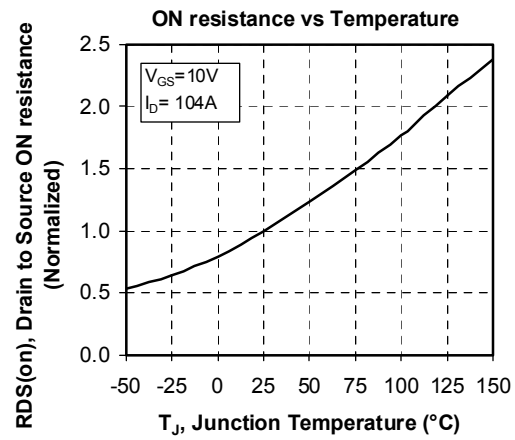
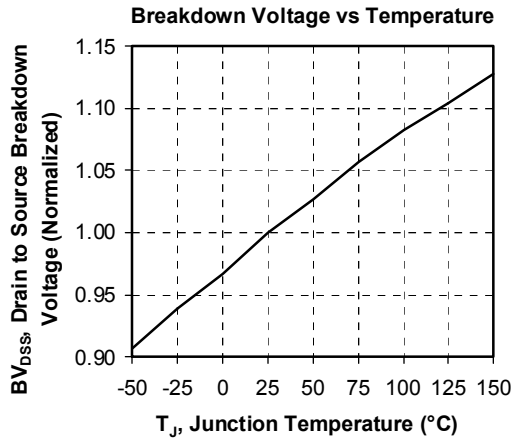


ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS: ± 0.1

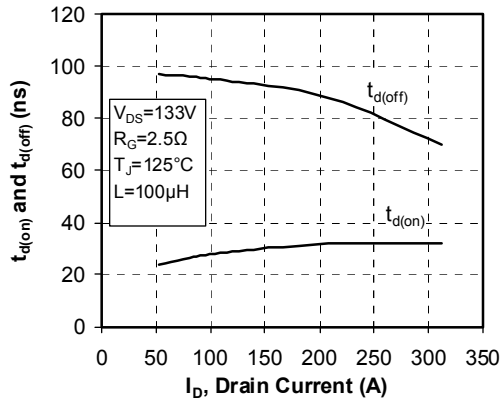
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve

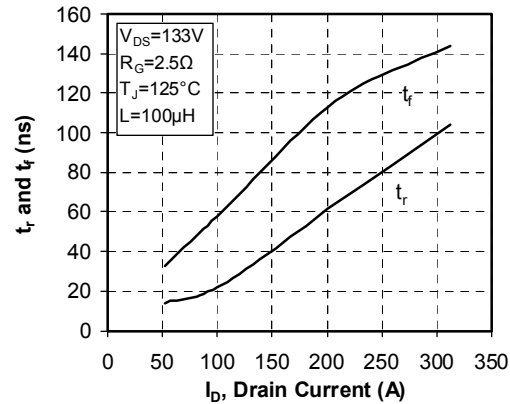




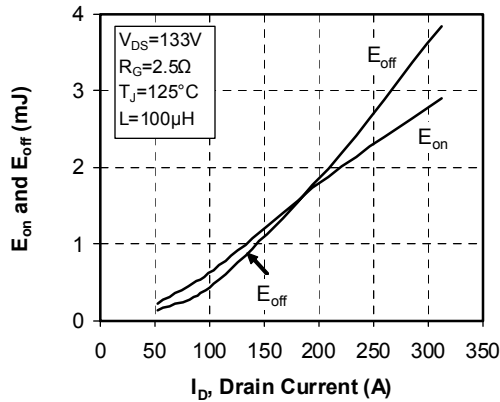
Delay Times vs Current



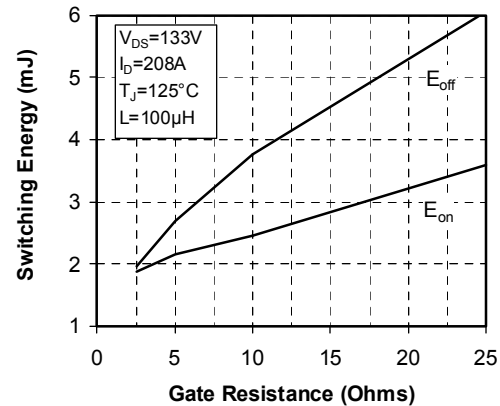
Rise and Fall times vs Current



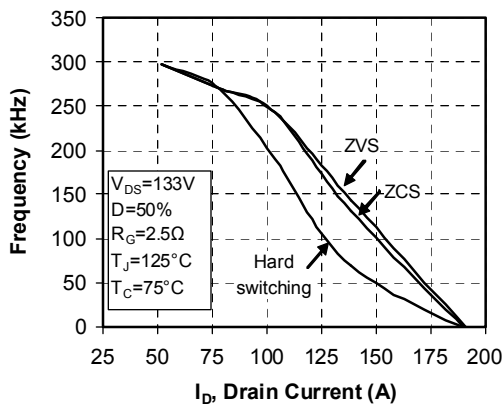
Switching Energy vs Current



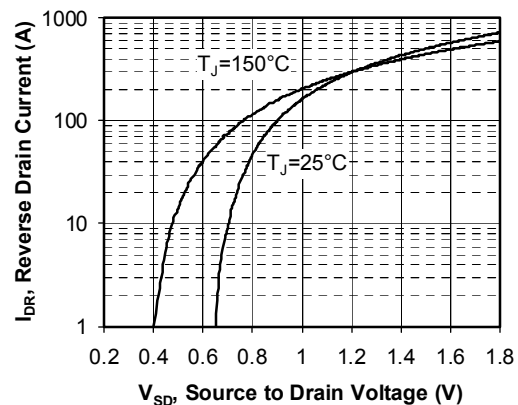
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.